74HC126-Q100; 74HCT126-Q100

Quad buffer/line driver; 3-state

Rev. 1 — 20 March 2013

Product data sheet

1. General description

The 74HC126-Q100; 74HCT126-Q100 is a quad buffer/line driver with 3-state outputs controlled by the output enable inputs (nOE). A LOW on nOE causes the outputs to assume a high impedance OFF-state. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} .

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Inverting outputs
- Complies with JEDEC standard no. 7A
- Input levels:
 - ♦ For 74HC126-Q100: CMOS level
 - ◆ For 74HCT126-Q100: TTL level
- ESD protection:
 - MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ♦ MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Multiple package options

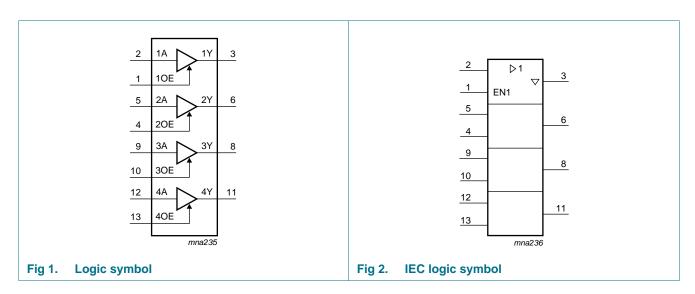
3. Ordering information

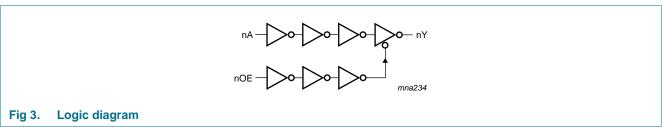
Table 1. Ordering information

Type number	Package											
	Temperature range	Name	Description	Version								
74HC126D-Q100	-40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body	SOT108-1								
74HCT126D-Q100			width 3.9 mm									
74HC126PW-Q100	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package;	SOT402-1								
74HCT126PW-Q100			14 leads; body width 4.4 mm									



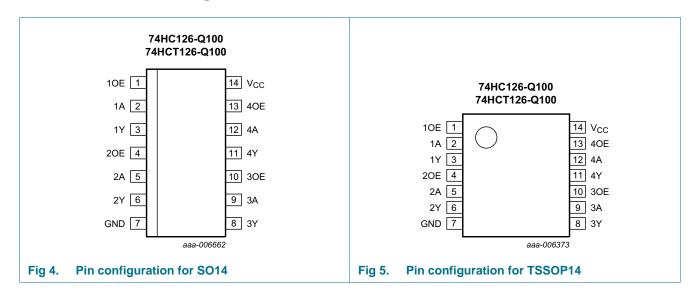
4. Functional diagram





5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
10E, 20E, 30E, 40E	1, 4, 10, 13	data enable input (active HIGH)
1A, 2A, 3A, 4A	2, 5, 9, 12	data input
1Y, 2Y, 3Y, 4Y	3, 6, 8, 11	data output
GND	7	ground (0 V)
V _{CC}	14	supply voltage

6. Functional description

Table 3. Function selection[1]

Inputs nOE	Output	
nOE	nA	nY
Н	L	L
Н	Н	Н
L	X	Z

^[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Parameter	Conditions	Min	Max	Unit
supply voltage		-0.5	+7	V
input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> -	±20	mA
output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> -	±20	mA
output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±35	mA
supply current		-	70	mA
ground current		-70	-	mA
storage temperature		-65	+150	°C
total power dissipation	SO14 and TSSOP14 packages	[2] -	500	mW
	supply voltage input clamping current output clamping current output current supply current ground current storage temperature	supply voltage $ \begin{array}{ll} \text{input clamping current} & V_1 < -0.5 \text{ V or } V_1 > V_{CC} + 0.5 \text{ V} \\ \text{output clamping current} & V_0 < -0.5 \text{ V or } V_0 > V_{CC} + 0.5 \text{ V} \\ \text{output current} & -0.5 \text{ V} < V_0 < V_{CC} + 0.5 \text{ V} \\ \text{supply current} \\ \text{ground current} \\ \text{storage temperature} \\ \end{array} $	$\begin{array}{cccccccccccccccccccccccccccccccccccc$	supply voltage $ -0.5 +7 $ input clamping current $ V_1 < -0.5 \text{ V or } V_1 > V_{CC} + 0.5 \text{ V } $ input clamping current $ V_0 < -0.5 \text{ V or } V_0 > V_{CC} + 0.5 \text{ V } $ output clamping current $ -0.5 \text{ V} < V_0 < V_{CC} + 0.5 \text{ V } $ supply current $ -0.5 \text{ V} < V_0 < V_{CC} + 0.5 \text{ V } $ $ - \pm 35 $ supply current $ -70 $ ground current $ -70 $ storage temperature $ -65 $

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

^[2] For SO14 package: P_{tot} derates linearly with 8 mW/K above 70 °C. For TSSOP14 packages: P_{tot} derates linearly with 5.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74F	IC126-Q	100	74H	CT126-C	100	Unit
			Min	Тур	Max	Min	Тур	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
Vo	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CC} = 2.0 \text{ V}$	-	-	625	-	-	-	ns/V
		V _{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 \text{ V}$	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	T _{ar}	_{nb} = 25	S °C		-40 °C 85 °C	T _{amb} = to +1	Unit	
			Min	Тур	Max	Min	Max	Min	Max	
74HC12	6-Q100									
V_{IH}	HIGH-level	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V_{IL}	LOW-level	V _{CC} = 2.0 V	-	8.0	0.5	-	0.5	-	0.5	V
	input voltage	V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -20 \mu A; V_{CC} = 6.0 V$	5.9	6.0	-	5.9	-	5.9	-	V
		$I_{O} = -6.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.98	4.32	-	3.84	-	3.7	-	V
		$I_{O} = -7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.48	5.81	-	5.34	-	5.2	-	V
V_{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 6.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
		$I_O = 7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	V
II	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ

 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Tar	_{mb} = 25	°C		-40 °C 85 °C	T _{amb} = to +	= −40 °C 125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
I _{OZ}	OFF-state output current	per input pin; $V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; other inputs at V_{CC} or GND; $V_{CC} = 6.0 \text{ V}$; $I_O = 0 \text{ A}$	-	±0.5	-	±5.0	-	±10	-	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	8.0	-	80	-	160	μΑ
Cı	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT1	26-Q100									
V_{IH}	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	1.6	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	1.2	8.0	-	0.8	-	0.8	V
V _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		$I_0 = -6.0 \text{ mA}$	3.98	4.32	-	3.84	-	3.7	-	V
V_{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_0 = 20 \mu A;$	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 6.0 \text{ mA};$	-	0.16	0.26	-	0.33	-	0.4	V
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μА
l _{OZ}	OFF-state output current	per input pin; $V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; other inputs at V_{CC} or GND; $V_{CC} = 5.5 \text{ V}$; $I_O = 0 \text{ A}$	-	-	±0.5	-	±5.0	-	±10	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	8.0	-	80	-	160	μА
Δl _{CC}	additional supply current	per input pin; $I_O = 0$ A; $V_I = V_{CC} - 2.1$ V; other inputs at V_{CC} or GND; $V_{CC} = 4.5$ V to 5.5 V								
		nA, nOE inputs	-	100	360	-	450	-	490	μΑ
Cı	input capacitance		-	3.5	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

 $GND = 0 \text{ V; } C_L = 50 \text{ pF; for test circuit see } Figure 8.$

Symbol	Parameter	Conditions		Tar	_{nb} = 25	S°C	$T_{amb} = -40^{\circ}$	°C to +125 °C	Unit	
				Min	Тур	Max	Max (85 °C)	Max (125 °C)		
74HC12	6-Q100									
t _{pd}	propagation delay	nA to nY; see Figure 6	[1]							
		$V_{CC} = 2.0 \text{ V}$		-	30	100	125	150	ns	
		$V_{CC} = 4.5 \text{ V}$		-	11	20	25	30	ns	
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	9	-	-	-	ns	
		$V_{CC} = 6.0 \text{ V}$		-	9	17	21	26	ns	
t _{en}	enable time	nOE to nY; see Figure 7	<u>[1]</u>							
		$V_{CC} = 2.0 \text{ V}$		-	41	125	155	190	ns	
		$V_{CC} = 4.5 \text{ V}$		-	15	25	31	38	ns	
		$V_{CC} = 6.0 \text{ V}$		-	12	21	26	32	ns	
t _{dis}	disable time	nOE to nY; see Figure 7	<u>[1]</u>							
		$V_{CC} = 2.0 \text{ V}$		-	41	125	155	190	ns	
		$V_{CC} = 4.5 \text{ V}$		-	15	25	31	38	ns	
		$V_{CC} = 6.0 \text{ V}$		-	12	21	26	32	ns	
t _t	transition time	see Figure 6	[1]							
		$V_{CC} = 2.0 \text{ V}$		-	14	60	75	90	ns	
		$V_{CC} = 4.5 \text{ V}$		-	5	12	15	18	ns	
		$V_{CC} = 6.0 \text{ V}$		-	4	10	13	15	ns	
C_{PD}	power dissipation capacitance	per package; V _I = GND to V _{CC}	[2]	-	23	-	-	-	pF	
74HCT1	26-Q100									
t _{pd}	propagation delay	nA to nY; see Figure 6	[1]							
		$V_{CC} = 4.5 \text{ V}$		-	14	24	30	36	ns	
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	11	-	-	-	ns	
t _{en}	enable time	nOE to nY; see Figure 7	<u>[1]</u>							
		$V_{CC} = 4.5 \text{ V}$		-	13	25	31	38	ns	
t _{dis}	disable time	nOE to nY; see Figure 7	<u>[1]</u>							
		$V_{CC} = 4.5 \text{ V}$		-	18	28	35	42	ns	
t _t	transition time	V _{CC} = 4.5 V; see <u>Figure 6</u>	<u>[1]</u>	-	5	12	15	18	ns	

Table 7. Dynamic characteristics

 $GND = 0 \ V; \ C_L = 50 \ pF;$ for test circuit see <u>Figure 8</u>.

	· - · ·							
Symbol	Parameter	Conditions	Tar	_{nb} = 25	°C	T _{amb} = -40 °	C to +125 °C	Unit
			Min	Тур	Max	Max (85 °C)	Max (125 °C)	
C_{PD}	power dissipation capacitance	per package; $V_I = \text{GND to V}_{CC} - 1.5 \text{ V}$	-	24	-	-	-	pF

[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

t_{en} is the same as t_{PZL} and t_{PZH}.

 t_{dis} is the same as t_{PLZ} and t_{PHZ} .

 t_{t} is the same as t_{THL} and $t_{\text{TLH}}.$

[2] C_{PD} is used to determine the dynamic power dissipation (P_D in μW):

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

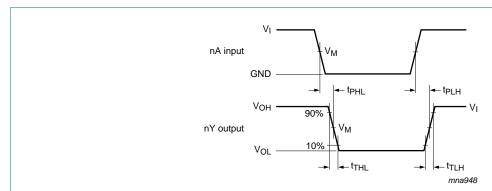
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\sum \left(C_L \times V_{CC}{}^2 \times f_o \right)$ = sum of outputs.

11. Waveforms



Measurement points are given in Table 8.

 $V_{\mbox{\scriptsize OL}}$ and $V_{\mbox{\scriptsize OH}}$ are typical voltage output levels that occur with the output load.

Fig 6. Input to output propagation delays

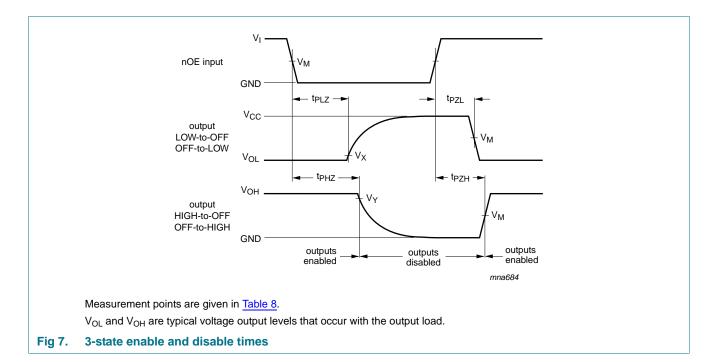
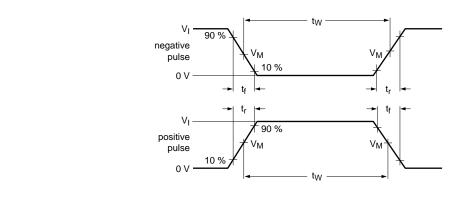
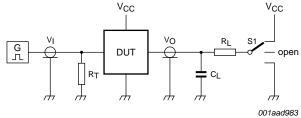


Table 8. Measurement points

Туре	Input	Output		
	V _M	V _M	V _X	V _Y
74HC126-Q100	0.5V _{CC}	0.5V _{CC}	0.1V _{CC}	0.9V _{CC}
74HCT126-Q100	1.3 V	1.3 V	0.1V _{CC}	0.9V _{CC}

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Test data is given in Table 9.

Definitions test circuit:

 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator

C_L = Load capacitance including jig and probe capacitance

R_L = Load resistance

S1 = Test selection switch

Fig 8. Test circuit for measuring switching times

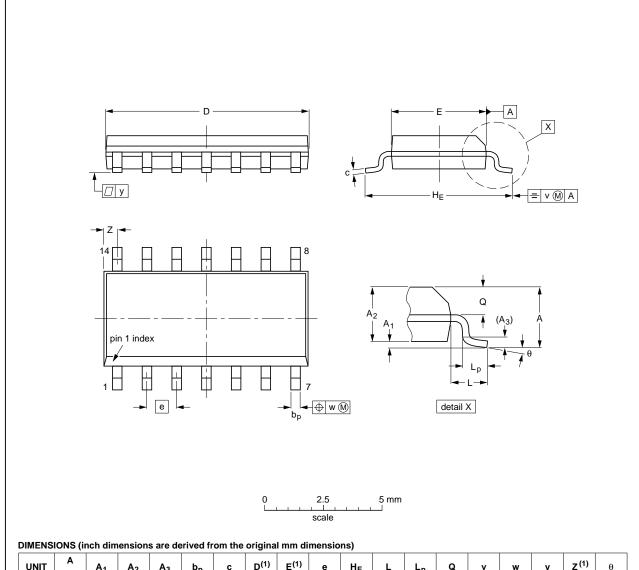
Table 9. Test data

Туре	Input		Load		S1 position			
	VI	t _r , t _f	C _L	R _L	t _{PHL} , t _{PLH}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}	
74HC126-Q100	V_{CC}	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}	
74HCT126-Q100	3 V	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}	

12. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01	1	0.0100 0.0075	0.35 0.34	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	0°

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT108-1	076E06	MS-012				99-12-27 03-02-19

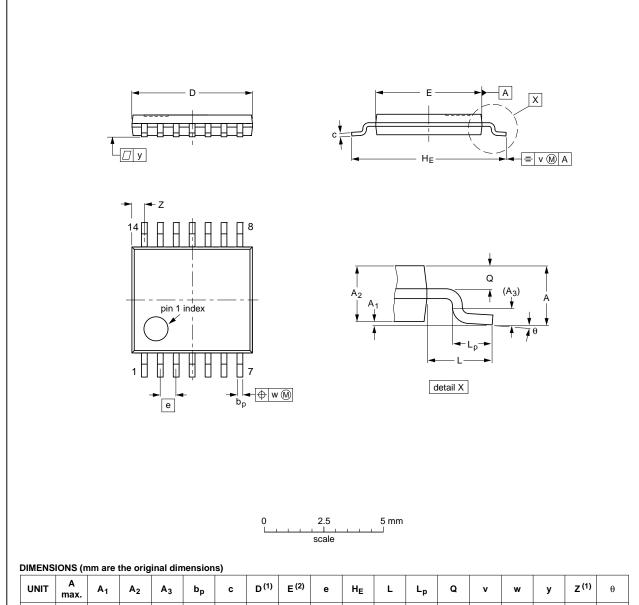
Fig 9. Package outline SOT108-1 (SO14)

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TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E (2)	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

PROJECTION ISSUE DATE
99-12-27 03-02-18

Fig 10. Package outline SOT402-1 (TSSOP14)

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13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MIL	Military
MM	Machine Model

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT126_Q100 v.1	20130320	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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74HC_HCT126_Q100

74HC126-Q100; 74HCT126-Q100

NXP Semiconductors

Quad buffer/line driver; 3-state

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